

Schottky barrier diode

RB521G-30

●Application

Rectifying small power

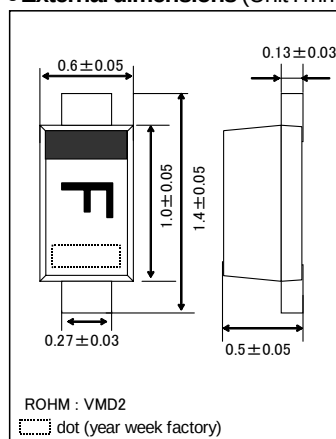
●Features

- 1) Ultra small mold type. (VMD2)
- 2) Low V_F
- 3) High reliability

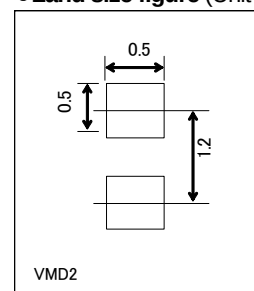
●Construction

Silicon epitaxial planer

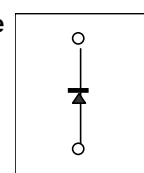
●External dimensions (Unit : mm)



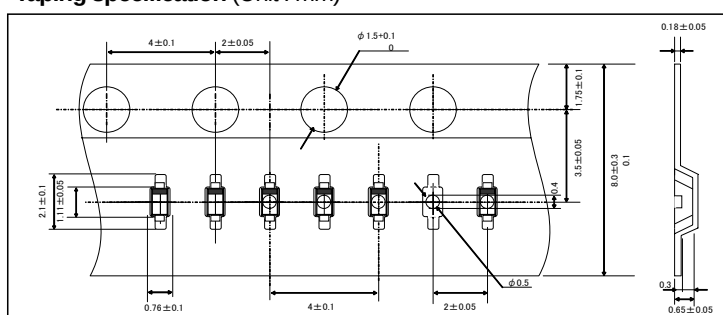
●Land size figure (Unit : mm)



●Structure



●Taping specification (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_O	100	mA
Forward current surge peak (60Hz·1cyc)	I_{FSM}	500	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.35	V	$I_F=10\text{mA}$
Reverse current	I_R	-	-	10	μA	$V_R=10\text{V}$

Diodes

●Electrical characteristic curves (Ta=25°C)

